2MBI100XAA120-50

IGBT Modules

Power Module (X series)
1200V / 100A / 2-in-1 package

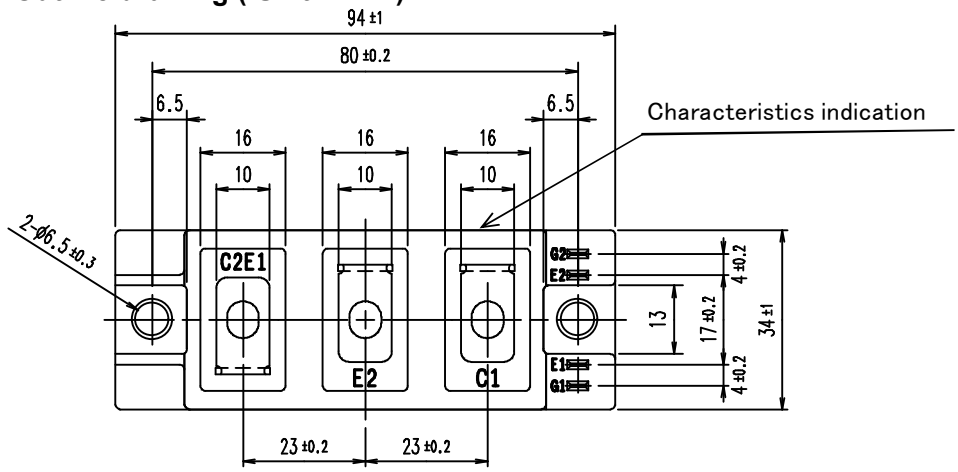
■ Features

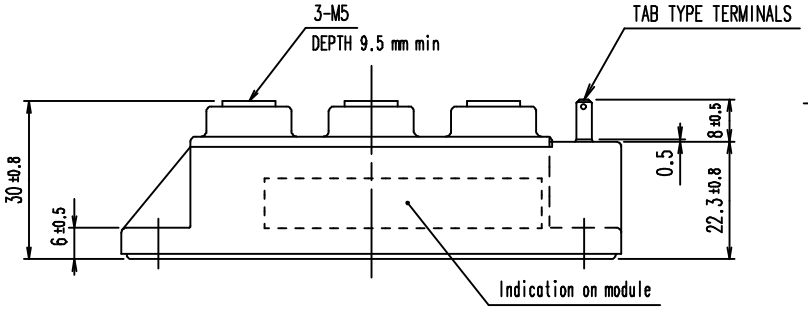
Low $V_{CE(sat)}$
High speed switching
Low Inductance Module structure

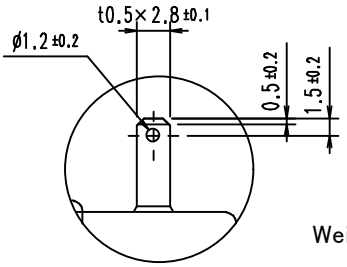
■ Applications

Inverter for Motor Drives, AC and DC Servo Drives
Uniterruptible Power Supply Systems,
Industrial machines,such as Welding machines

■ Outline drawing (Unit : mm)



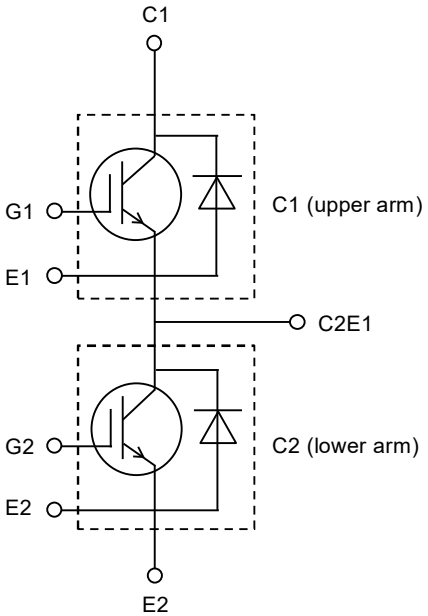




DETAIL TAB TYPE TERMINALS

Weight: 180 g(typ.)

■ Equivalent circuit



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2MBI100XAA120-50

■ Absolute maximum ratings (at T_c= 25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units
Inverter	Collector-Emitter voltage,Gate-Emitter short-circuited	V_{CES}			1200	V
	Gate-Emitter voltage,Collector-Eemitter short-circuited	V_{GES}			±20	V
	Collector current	I_C	Continuous	T_c=100°C	100	A
	Repetitive peak collector current	I_{CRM}	1ms		200	
	Forward current	I_F			100	
	Repetitive peak forward current	I_{FRM}	1ms		200	
	Total power dissipation	P_{tot}	1 device		530	W
	Virtual junction temperature	T_{vj}			175	°C
	Operating virtual junction temperature	T_{vjop}			175	
Case temperature		T_c			125	
Storage temperature		T_{stg}			-40 ~ 125	
Isolation voltage	Between terminals and copper base (*1)	V_{isol}	AC: 1min.		4000	Vrms
Mounting torque of screws to heatsink		M_s	M5		3.0 ~ 5.0	N·m
Mounting torque of screws to terminals		M_t	M5		2.5 ~ 5.0	

(*1) All terminals should be connected together during the test.

2MBI100XAA120-50

■ Electrical characteristics (at T_{vj}= 25°C unless otherwise specified)

	Items	Symbols	Conditions		Characteristics min.	Characteristics typ.	Characteristics max.	Units
Inverter	Collector-Emitter cut-off current,Gate-Emitter short-circuited	I_{CES}	V_{GE} = 0V V_{CE} = 1200V		-	-	50	μA
	Gate leakage current,Collector-Emitter short-circuited	I_{GES}	V_{CE}=0V, V_{GE}=±20V		-	-	100	nA
	Gate-Emitter threshold voltage	$V_{GE(th)}$	V_{CE} = 20V I_C = 100mA		6.0	6.5	7.0	V
	Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	V_{GE} = 15V I_C= 100A	T_{vj}=25°C	-	1.60	2.05	V
		$V_{CE(sat)}$ (chip)		T_{vj}=25°C	-	1.40	1.85	
				T_{vj}=125°C	-	1.70	-	
				T_{vj}=150°C	-	1.80	-	
				T_{vj}=175°C	-	1.85	-	
	Internal gate resistance	r_g	-		-	9.00	-	Ω
	Input capacitance	C_{ies}	V_{CE}=10V, V_{GE}=0V, f=1MHz		-	12	-	nF
	Output capacitance	C_{oes}			-	0.4	-	
	Reverse transfer capacitance	C_{res}			-	0.10	-	
	Gate charge	Q_G	V_{CC} = 600V, I_C = 100A V_{GE} = -15 → +15V		-	0.7	-	μC
	Forward voltage	V_F (terminal)	V_{GE} = 0V I_F= 100A	T_{vj}=25°C	-	1.80	2.25	V
		V_F (chip)		T_{vj}= 25°C	-	1.60	2.05	
				T_{vj}=125°C	-	1.65	-	
				T_{vj}=150°C	-	1.60	-	
				T_{vj}=175°C	-	1.60	-	
	Turn-on delay time(*1)	$t_{d(on)}$	V_{CC} = 600V I_C, I_F = 100A V_{GE} = +15/ -15V R_G = 5.6 Ω L_S = 30 nH	T_{vj}= 25°C	-	0.34	-	μs
				T_{vj}=125°C	-	0.38	-	
				T_{vj}=150°C	-	0.38	-	
				T_{vj}=175°C	-	0.39	-	
	Rise time(*1)	t_r		T_{vj}= 25°C	-	0.07	-	
				T_{vj}=125°C	-	0.09	-	
				T_{vj}=150°C	-	0.09	-	
				T_{vj}=175°C	-	0.09	-	
	Turn-off delay time(*1)	$t_{d(off)}$		T_{vj}= 25°C	-	0.31	-	
				T_{vj}=125°C	-	0.36	-	
				T_{vj}=150°C	-	0.37	-	
				T_{vj}=175°C	-	0.51	-	
	Fall time(*1)	t_f		T_{vj}= 25°C	-	0.16	-	
				T_{vj}=125°C	-	0.25	-	
				T_{vj}=150°C	-	0.27	-	
				T_{vj}=175°C	-	0.26	-	
	Reverse recovery time	t_{rr}		T_{vj}= 25°C	-	0.48	-	
				T_{vj}=125°C	-	0.60	-	
				T_{vj}=150°C	-	0.63	-	
				T_{vj}=175°C	-	0.70	-	

(*1) Turn-on time (t_{on}) = $t_{d(on)}$+ t_r , Turn-off time (t_{off}) = $t_{d(off)}$ + t_f

■ Electrical characteristics (at T_{vj}= 25°C unless otherwise specified)

Items		Symbols	Conditions		Characteristics min.	Characteristics typ.	Characteristics max.	Units
Inverter	Turn-on energy	E_{on}	V_{CC} = 600V I_C, I_F = 100A V_{GE} = +15/ -15V R_G = 5.6 Ω L_S = 30 nH	T_{vj}=25°C	-	8.6	-	mJ
				T_{vj}=125°C	-	12.7	-	
				T_{vj}=150°C	-	13.7	-	
				T_{vj}=175°C	-	15.3	-	
	Turn-off energy	E_{off}		T_{vj}=25°C	-	7.4	-	
				T_{vj}=125°C	-	9.7	-	
				T_{vj}=150°C	-	10.2	-	
				T_{vj}=175°C	-	10.8	-	
	Reverse recovery energy	E_{rr}		T_{vj}=25°C	-	2.4	-	
				T_{vj}=125°C	-	4.9	-	
				T_{vj}=150°C	-	5.5	-	
				T_{vj}=175°C	-	6.5	-	

NOTICE:
The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment. We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

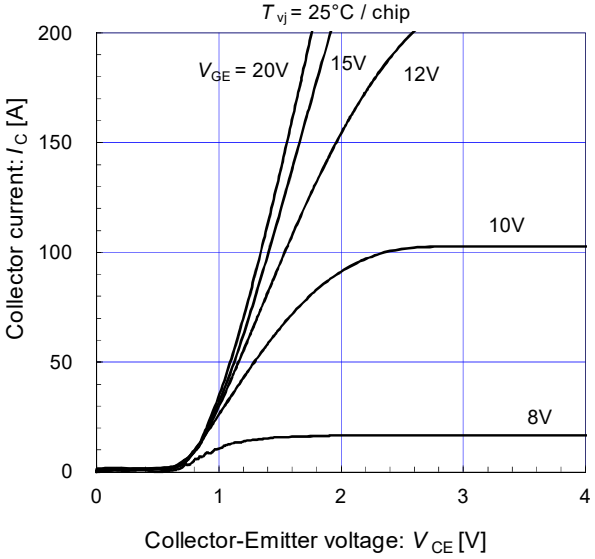
■Thermal resistance characteristics

	Symbols	Conditions	Characteristics min.	Characteristics typ.	Characteristics max.	ns
Thermal resistance junction to case (1device)	$R_{th(j-c)}$	IGBT	-	-	0.281	K/W
		FWD	-	-	0.550	
Thermal resistance case to heatsink (1IGBT + 1FWD) (*1)	$R_{th(c-s)}$	with 1 W/(m·K) thermal grease	-	0.050	-	

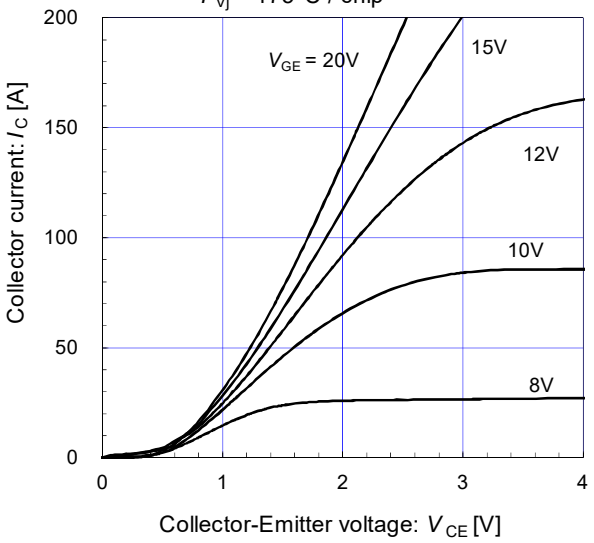
(*1) This is the value which is defined mounting on the additional heatsink with thermal grease.

2MBI100XAA120-50

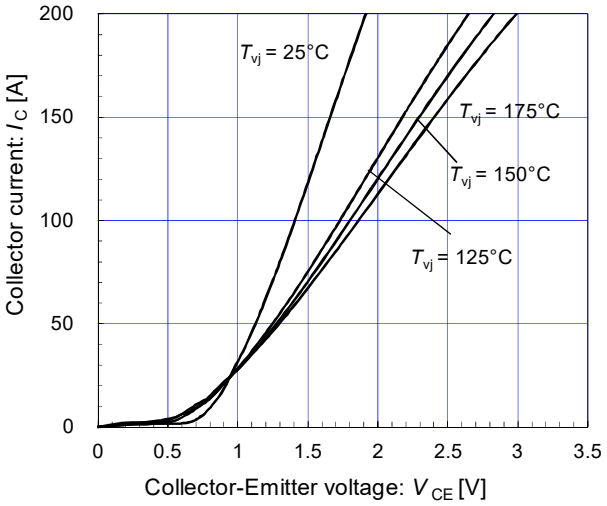
[Inverter]
Collector current vs. Collector-Emitter voltage (typ.)
T_{vj} = 25°C / chip



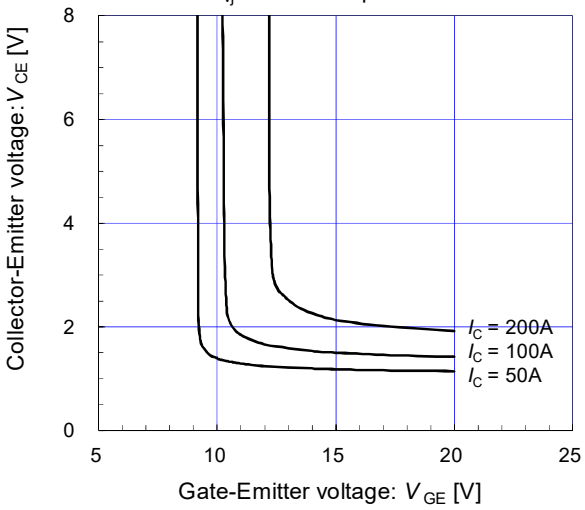
[Inverter]
Collector current vs. Collector-Emitter voltage (typ.)
T_{Vj} = 175°C / chip



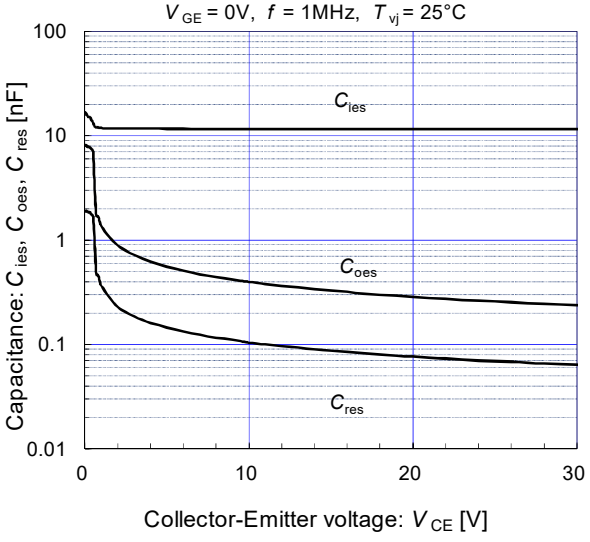
[Inverter]
Collector current vs. Collector-Emitter voltage (typ.)
V_{GE} = 15V / chip



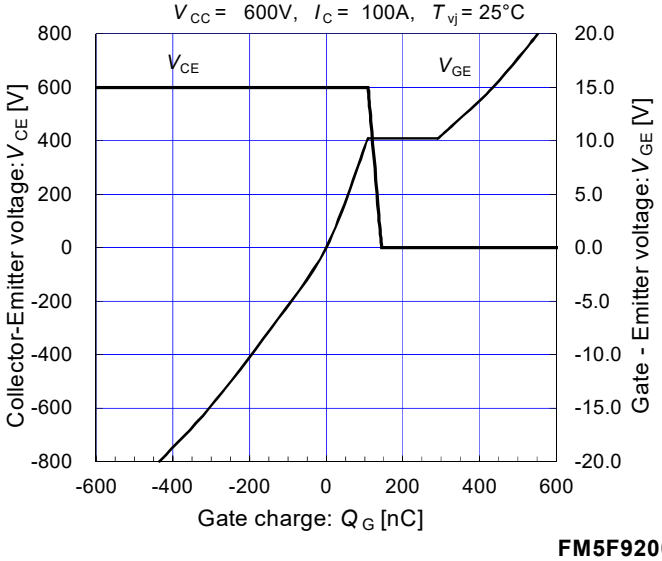
[Inverter]
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)
T_{vj} = 25°C / chip



[Inverter]
Capacitance vs. Collector-Emitter voltage (typ.)
V_{GE} = 0V, f = 1MHz, T_{vj} = 25°C

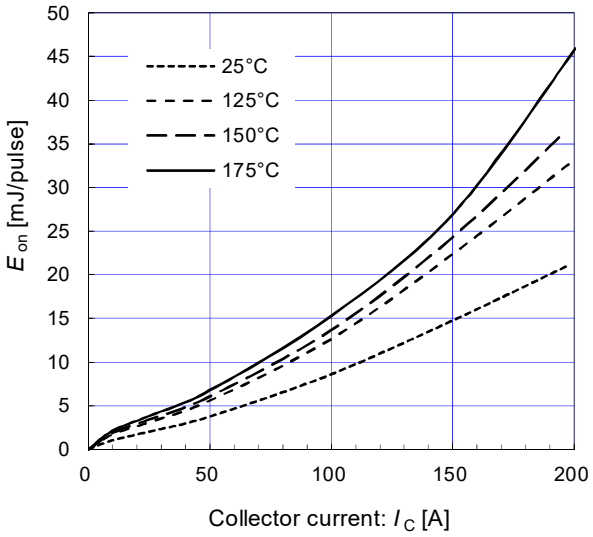


[Inverter]
Dynamic gate charge (typ.)
V_{CC} = 600V, I_C = 100A, T_{vj} = 25°C

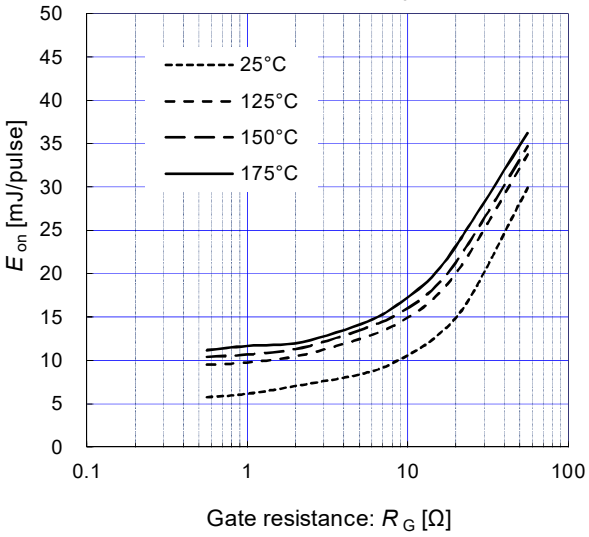


2MBI100XAA120-50

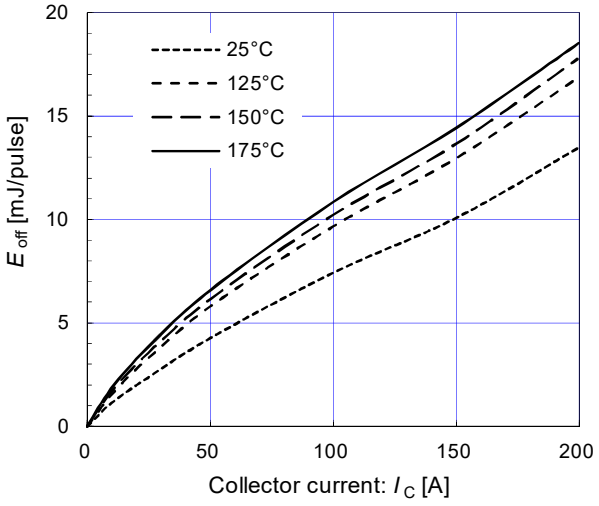
[Inverter]
E_{on} vs. Collector current (typ.)
V_{CC} = 600V, V_{GE} = +15/ -15V, R_G = 5.6 Ω



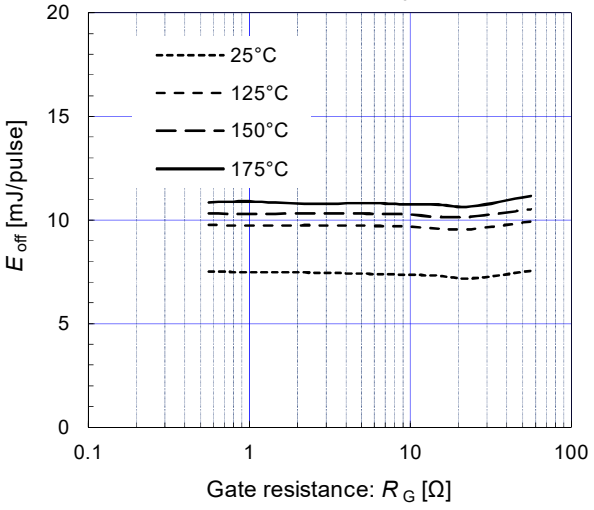
[Inverter]
E_{on} vs. Gate resistance (typ.)
V_{CC} = 600V, V_{GE} = +15/ -15V, I_C = 100A



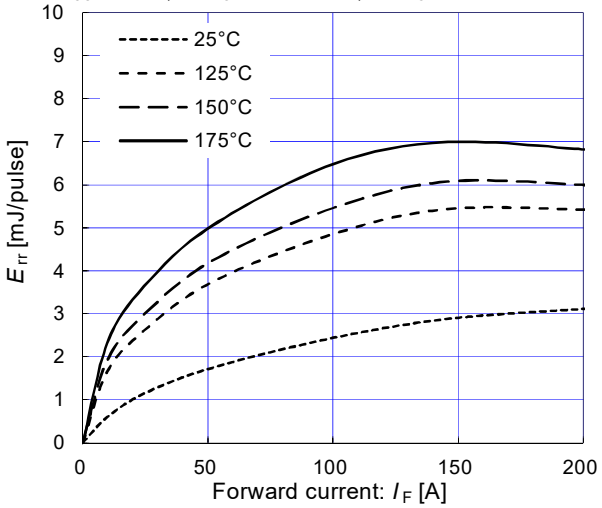
[Inverter]
E_{off} vs. Collector current (typ.)
V_{CC} = 600V, V_{GE} = +15/ -15V, R_G = 5.6 Ω



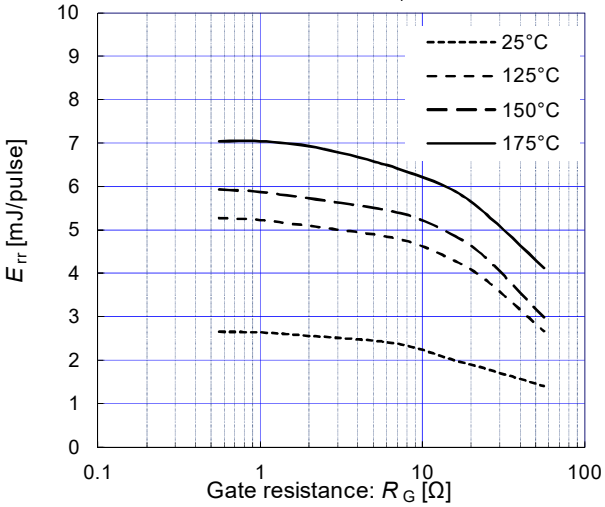
[Inverter]
E_{off} vs. Gate resistance (typ.)
V_{CC} = 600V, V_{GE} = +15/ -15V, I_C = 100A



[Inverter]
E_{rr} vs. Forward current (typ.)
V_{CC} = 600V, V_{GE} = +15/ -15V, R_G = 5.6 Ω

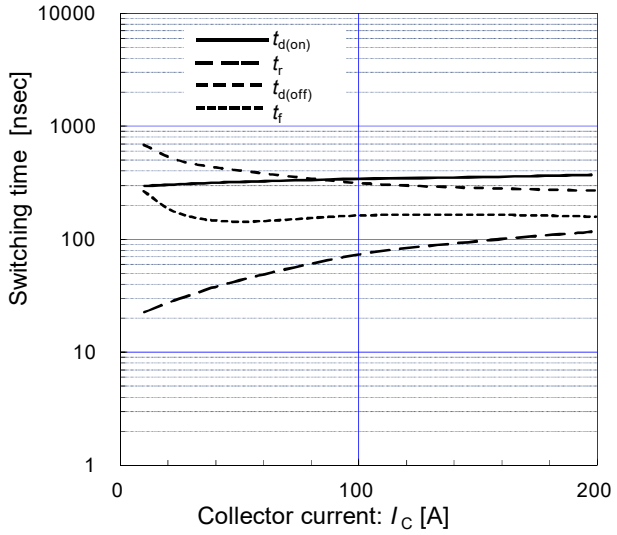


[Inverter]
E_{rr} vs. Gate resistance (typ.)
V_{CC} = 600V, V_{GE} = +15/ -15V, I_F = 100A

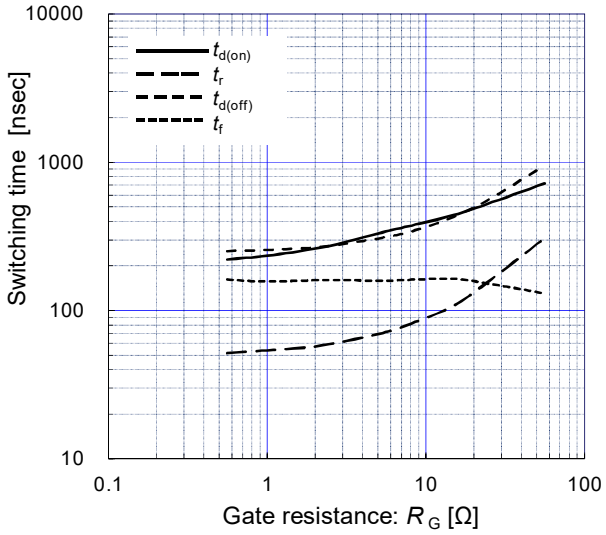


2MBI100XAA120-50

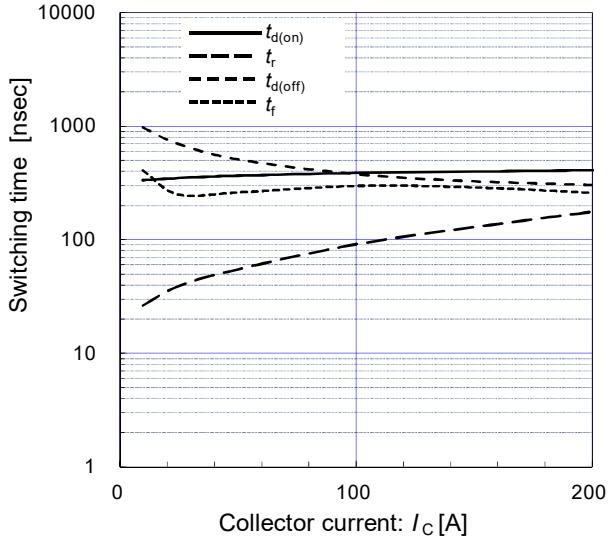
[Inverter]
Switching time vs. Collector current (typ.)
V_{CC} = 600V, R_G = 5.6 Ω, V_{GE} = +15/ -15V, T_{vj} = 25°C



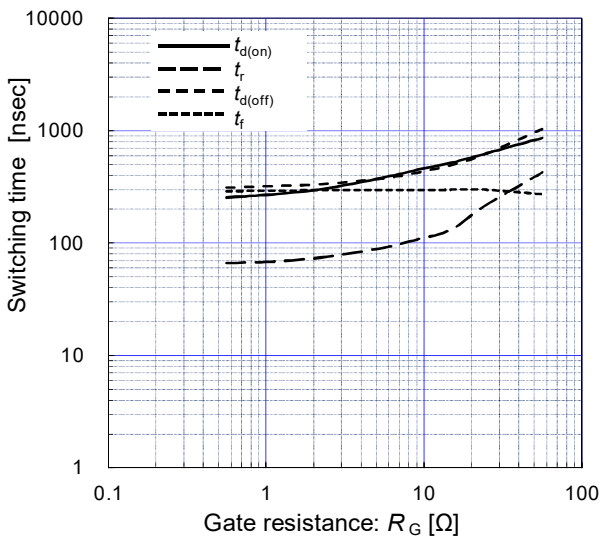
[Inverter]
Switching time vs. Gate resistance (typ.)
V_{CC} = 600V, I_C = 100A, V_{GE} = +15/ -15V, T_{vj} = 25°C



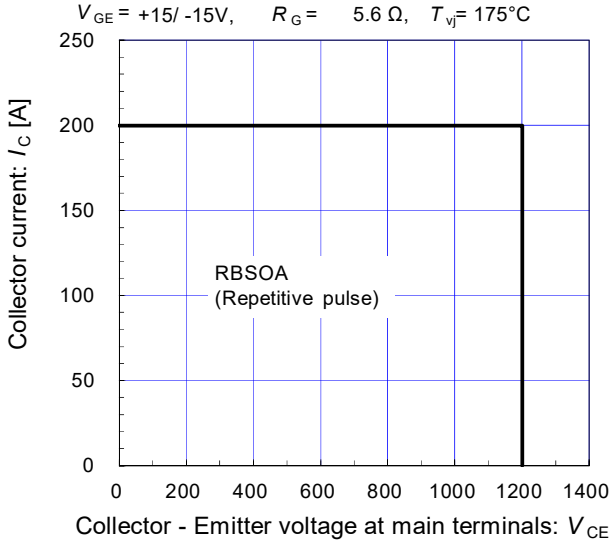
[Inverter]
Switching time vs. Collector current (typ.)
V_{CC} = 600V, R_G = 5.6 Ω, V_{GE} = +15/ -15V, T_{vj} = 175°C



[Inverter]
Switching time vs. Gate resistance (typ.)
V_{CC} = 600V, I_C = 100A, V_{GE} = +15/ -15V, T_{vj} = 175°C

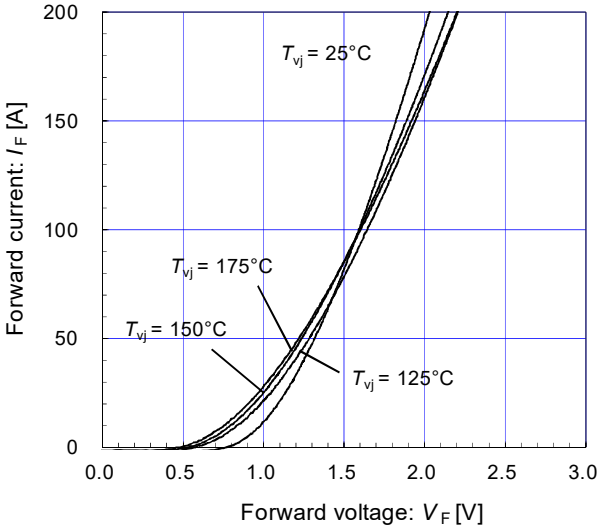


[Inverter]
Reverse bias safe operating area (max.)
V_{GE} = +15/ -15V, R_G = 5.6 Ω, T_{vj} = 175°C

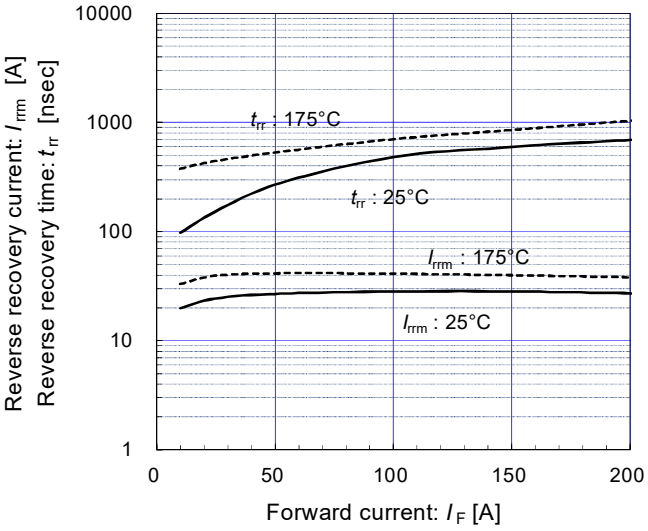


2MBI100XAA120-50

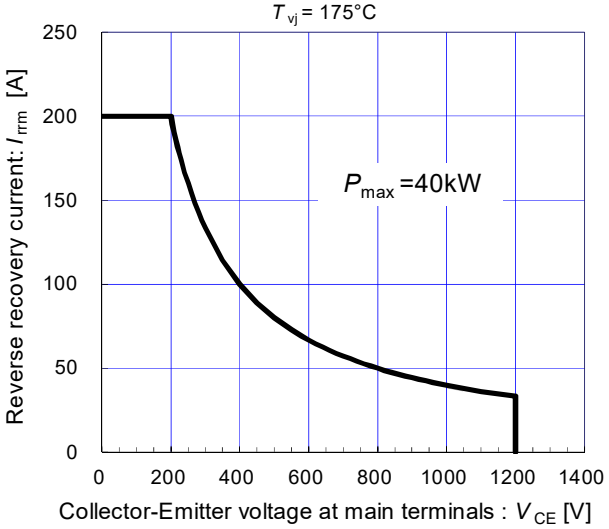
[Inverter]
Forward current vs. Forward voltage (typ.)
chip



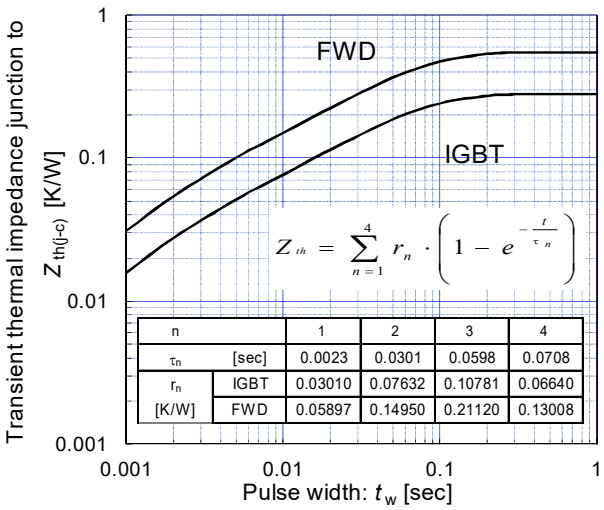
[Inverter]
Reverse recovery characteristics (typ.)
V_{CC} = 600V, V_{GE} = +15/ -15V, R_G = 5.6 Ω



[Inverter]
FWD safe operation area (max.)
T_{vj} = 175°C



[Inverter]
Transient thermal resistance(max.)



n		1	2	3	4
τ_n	[sec]	0.0023	0.0301	0.0598	0.0708
r_n [K/W]	IGBT	0.03010	0.07632	0.10781	0.06640
	FWD	0.05897	0.14950	0.21120	0.13008

Warnings

1. This Catalog contains the product specifications, characteristics, data, materials, and structures as of 10/2023. The contents are subject to change without notice for specification changes or other reasons. When using a product listed in this Catalog, be sure to obtain the latest specifications.

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4. The products introduced in this Catalog are intended for use in the following electronic and electrical equipment which has normal reliability requirements.
・Computers ・OA equipment ・Communications equipment (terminal devices) ・Measurement equipment
・Machine tools ・Audiovisual equipment ・Electrical home appliances ・Personal equipment ・Industrial robots etc.

5. If you need to use a product in this Catalog for equipment requiring higher reliability than normal, such as for the equipment listed below, it is imperative to contact Fuji Electric Co., Ltd. to obtain prior approval. When using these products for such equipment, take adequate measures such as a backup system to prevent the equipment from malfunctioning even if a Fuji's product incorporated in the equipment becomes faulty.
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・Traffic-signal control equipment ・Gas leakage detectors with an auto-shut-off feature
・Emergency equipment for responding to disasters and anti-burglary devices ・Safety devices ・Medical equipment

6. Do not use products in this Catalog for the equipment requiring strict reliability such as the following and equivalents to strategic equipment (without limitation).
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富士電機 Innovating Energy Technology

Technical Information

IGBT Modules

- Please refer to URLs below for futher information about products, application manuals and design support.
- 关于本规格书中没有记载的产品信息，应用手册，技术信息等，请参考以下链接。
- 本データシートに記載されていない製品情報，アプリケーションマニュアル，デザインサポートは以下のURLをご参照下さい。

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4 Design Support	www.fujielectric.com/products/semiconductor/model/igbt/technical/
5 Mounting Instructions	www.fujielectric.com/products/semiconductor/model/igbt/mounting/
6 IGBT Loss Simulation Software	www.fujielectric.com/products/semiconductor/model/igbt/simulation/
7 Fuji Electric Journal	www.fujielectric.com/products/semiconductor/journal/
8 Contact	www.fujielectric.com/contact/

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